Erratum to: Growth Behavior of Cubic Boron Nitride (cBN) Phase in B-C-N Film Deposited on Si Substrate with Non-Uniform Ion Flux

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On page 591, first paragraph, 3rd to 10th line, the following sentence should be now read as: In contrast to the diamond thin film with sp³-bonding which has been deposited by chemical vapor deposition (CVD) with a mixed gas of carbon source and hydrogen at a high temperature over 800 °C, the cBN phase has been mainly synthesized by physical vapor deposition (PVD) with an energetic ion source at a lower temperature below 600 °C, as in the case of transition metal (carbo) nitride coatings [14].